Speaker Profile

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Chungwoo Kim received the B. S. degree in inorganic materials engineering from the Hanyang University in 1986, and the M. S. and Ph. D. degrees in Materials Science & Engineering from the University of Utah, Salt Lake City, UT in 1990 and 1995, respectively. From 1995 to 1996, he worked as a post-doctoral fellow at electrical engineering dept. of University of Utah in the field of micro vacuum technology. In 1996, he joined the Samsung Advanced Institute of Technology (SAIT) in Korea. He is presently a principal research staff member and project manager for nanoscale nonvolatile memory devices at materials and devices Lab. of SAIT. Among his contributions and inventions are single elctron transistors and memories, a micromachined Si cavity resonator and mechanical switches for millimeter-wave oscillator applications and mobile communications. His current research activities include design, fabrication, and characterizations of nanoscale SONOS memory, charge transport mechanism and related measurement, and single elctron effects.

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